

Jiamin Xue

List of Publications by Year in descending order

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Version: 2024-02-01

22
papers

2,859
citations

758635

12
h-index

676716

22
g-index

22
all docs

22
docs citations

22
times ranked

5013
citing authors

#	ARTICLE	IF	CITATIONS
1	Scanning tunnelling microscopy and spectroscopy of ultra-flat graphene on hexagonal boron nitride. <i>Nature Materials</i> , 2011, 10, 282-285.	13.3	1,157
2	Emergence of superlattice Dirac points in graphene on hexagonal boron nitride. <i>Nature Physics</i> , 2012, 8, 382-386.	6.5	956
3	Two-Dimensional SnS: A Phosphorene Analogue with Strong In-Plane Electronic Anisotropy. <i>ACS Nano</i> , 2017, 11, 2219-2226.	7.3	239
4	Graphene on hexagonal boron nitride. <i>Journal of Physics Condensed Matter</i> , 2014, 26, 303201.	0.7	76
5	Field-effect transistors of high-mobility few-layer SnSe ₂ . <i>Applied Physics Letters</i> , 2016, 109, .	1.5	73
6	Interlayer Decoupling in 30° Twisted Bilayer Graphene Quasicrystal. <i>ACS Nano</i> , 2020, 14, 1656-1664.	7.3	64
7	Promotion of CO ₂ Electrochemical Reduction via Cu Nanodendrites. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 11562-11569.	4.0	54
8	Nb ₂ SiTe ₄ : A Stable Narrow-Gap Two-Dimensional Material with Ambipolar Transport and Mid-Infrared Response. <i>ACS Nano</i> , 2019, 13, 10705-10710.	7.3	48
9	Long-Wavelength Local Density of States Oscillations Near Graphene Step Edges. <i>Physical Review Letters</i> , 2012, 108, 016801.	2.9	37
10	Lateral Heterostructures Formed by Thermally Converting n-Type SnSe ₂ to p-Type SnSe. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 12831-12838.	4.0	37
11	Observation of ν -Valley Moiré Bands and Emergent Hexagonal Lattice in Twisted Transition Metal Dichalcogenides. <i>Physical Review X</i> , 2022, 12, .	2.8	18
12	Chemical Vapor Deposition Growth of Bernal-Stacked Bilayer Graphene by Edge-Selective Etching with H ₂ O. <i>Chemistry of Materials</i> , 2018, 30, 7852-7859.	3.2	17
13	One-Dimensional Metal Embedded in Two-Dimensional Semiconductor in Nb ₂ SiTe ₄ . <i>ACS Nano</i> , 2021, 15, 7149-7154.	7.3	14
14	Visualizing Band Profiles of Gate-Tunable Junctions in MoS ₂ /WSe ₂ Heterostructure Transistors. <i>ACS Nano</i> , 2021, 15, 16314-16321.	7.3	14
15	Large Photomultiplication by Charge-Self-Trapping for High-Response Quantum Dot Infrared Photodetectors. <i>ACS Applied Materials & Interfaces</i> , 2022, 14, 14783-14790.	4.0	12
16	Atomic bridge memristor based on silver and two-dimensional GeSe. <i>AIP Advances</i> , 2020, 10, 045003.	0.6	8
17	Isotropic charge screening of anisotropic black phosphorus revealed by potassium adatoms. <i>Physical Review B</i> , 2019, 100, .	1.1	7
18	Detecting band profiles of devices with conductive atomic force microscopy. <i>Review of Scientific Instruments</i> , 2020, 91, 073702.	0.6	7

#	ARTICLE	IF	CITATIONS
19	Anisotropic Infrared Response and Orientation-Dependent Strain-Tuning of the Electronic Structure in Nb ₂ SiTe ₄ . ACS Nano, 2022, 16, 8107-8115.	7.3	7
20	Observation of dimension-crossover of a tunable 1D Dirac fermion in topological semimetal NbSixTe2. Npj Quantum Materials, 2022, 7, .	1.8	7
21	Systematic investigation of electrical contact barriers between different electrode metals and layered GeSe. Applied Physics Letters, 2019, 114, 013505.	1.5	4
22	Raman spectroscopic study of artificially twisted and non-twisted trilayer graphene. Applied Physics Letters, 2021, 118, .	1.5	3